

I 0V Half Bridge Dual N-Channel Super Trench Power MOSFET

Description

The HM18SDN04D uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(on)}$ and Q_g . It includes two specialized MOSFETs in a dual Power DFN5x6 package.

General Features

Q1 "High Side" MOSFET

- $V_{DS} = I\ 0V, I_D = F\ A$
 $R_{DS(on)} < 16m\Omega @ V_{GS}=10V$
 $R_{DS(on)} < 24m\Omega @ V_{GS}=4.5V$

Q2 "Low Side" MOSFET

- $V_{DS} = I\ 0V, I_D = F\ A$
 $R_{DS(on)} < 16m\Omega @ V_{GS}=10V$
 $R_{DS(on)} < 24m\Omega @ V_{GS}=4.5V$

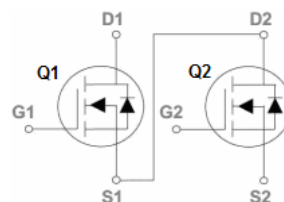
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb free terminal plating
- RoHS compliant
- Halogen free

Application

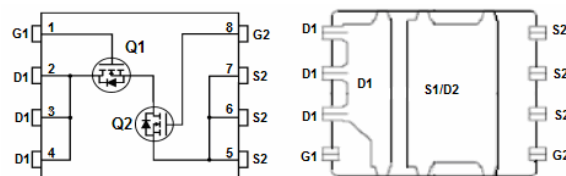
- Compact DC/DC converter applications

100% UIS TESTED!

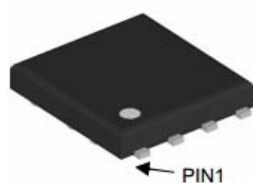
100% ΔV_{ds} TESTED!



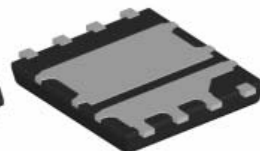
Schematic Diagram



pin assignment



Top View



Bottom View

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM18SDN04D	HM18SDN04D	DFN5X6-8L	330mm	12mm	5000 units

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Q1	Q2	Unit
Drain-Source Voltage	V_{DS}	10	10	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Drain Current-Continuous (Note 2)	$T_C=25^\circ\text{C}$	I_D	A	A
	$T_C=100^\circ\text{C}$	I_D	A	
Drain Current -Pulsed (Note 1)	I_{DM}	1	1	A
Power Dissipation	P_D	30	80	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	-55 To 150	$^\circ\text{C}$

Thermal Characteristic

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance, Junction-to-Case (Note 2) (Q1)	$R_{\theta JC}$	3.3	4.2	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case (Note 2) (Q2)	$R_{\theta JC}$	1.2	1.6	$^\circ\text{C/W}$

Q1 Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	10		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =10V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	1.5	2.2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =15A	-	12.9	16	mΩ
		V _{GS} =4.5V, I _D =15A	-	18.9	24	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =15A		30	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{ISS}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	822	-	PF
Output Capacitance	C _{OSS}		-	344	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	15.3	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, I _D =15A V _{GS} =10V, R _G =1.6Ω	-	6.5	-	nS
Turn-on Rise Time	t _r		-	2.5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	17	-	nS
Turn-Off Fall Time	t _f		-	2.5	-	nS
Total Gate Charge	Q _g	V _{DS} =15V, I _D =15A, V _{GS} =10V	-	15	-	nC
Gate-Source Charge	Q _{gs}		-	2.9		nC
Gate-Drain Charge	Q _{gd}		-	2.1		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =20A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-1000000		A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = I _S di/dt = 100A/μs (Note3)	-	11	-	nS
Reverse Recovery Charge	Q _{rr}		-	19	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : T_J=25°C, V_{DD}=15V, V_G=10V, L=0.5mH, R_G=25Ω

Q1 Typical Electrical and Thermal Characteristics

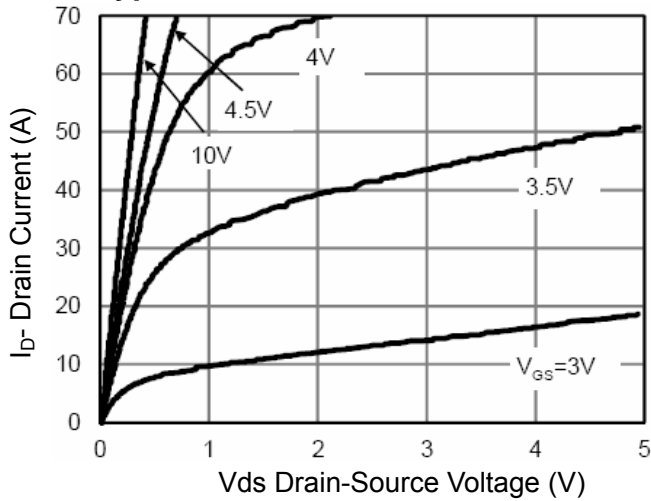


Figure 1 Output Characteristics

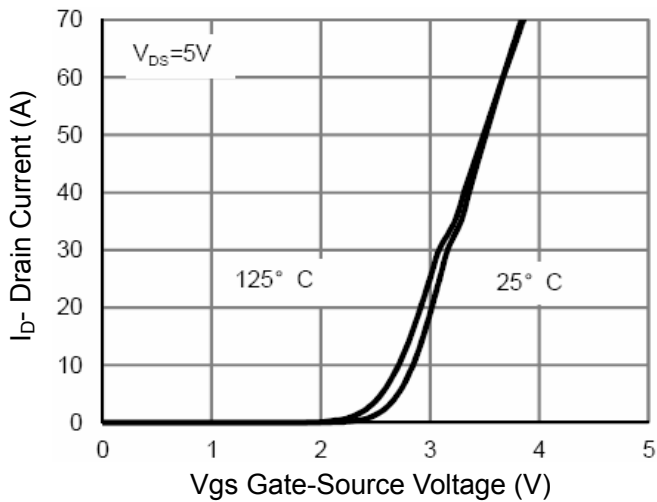


Figure 2 Transfer Characteristics

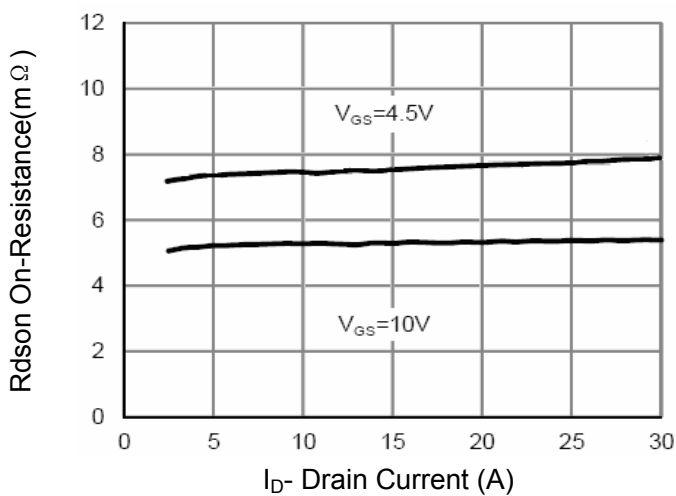


Figure 3 $R_{DS(on)}$ - Drain Current

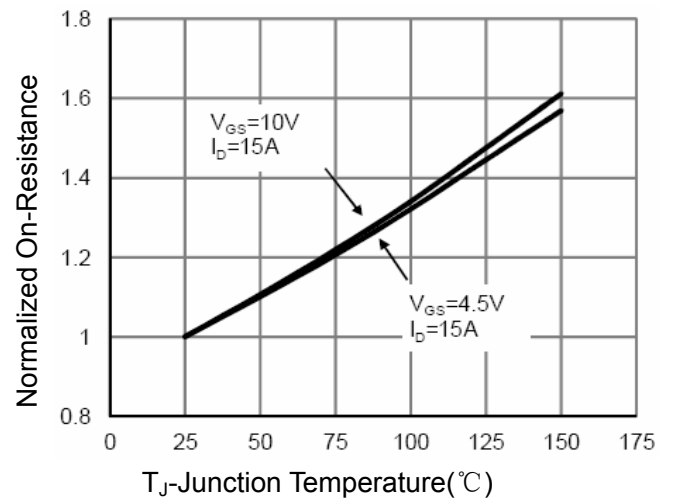


Figure 4 $R_{DS(on)}$ -Junction Temperature

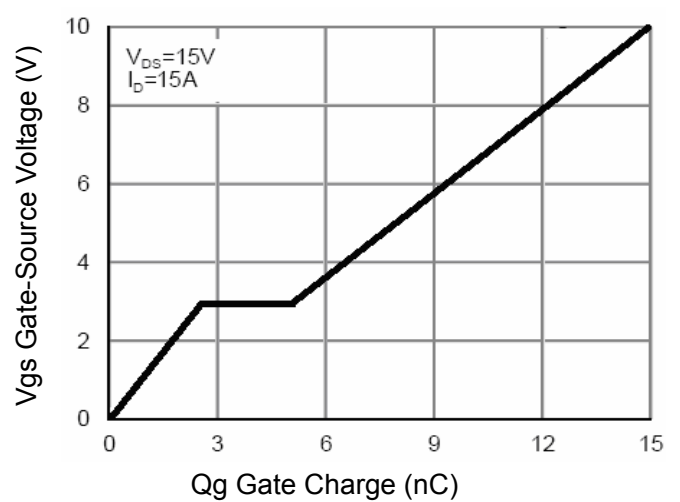


Figure 5 Gate Charge

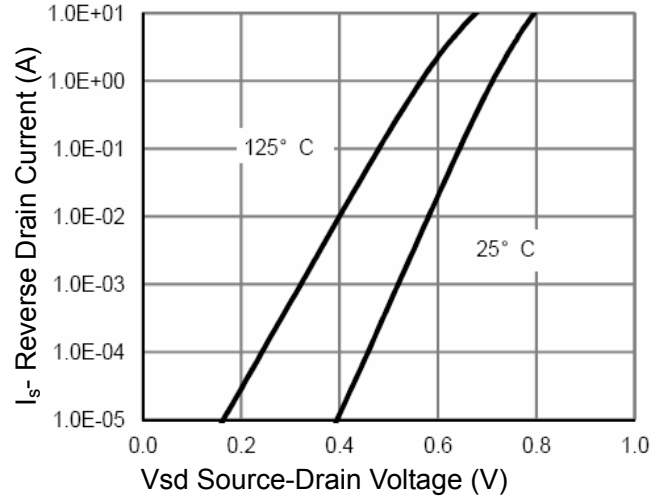


Figure 6 Source- Drain Diode Forward

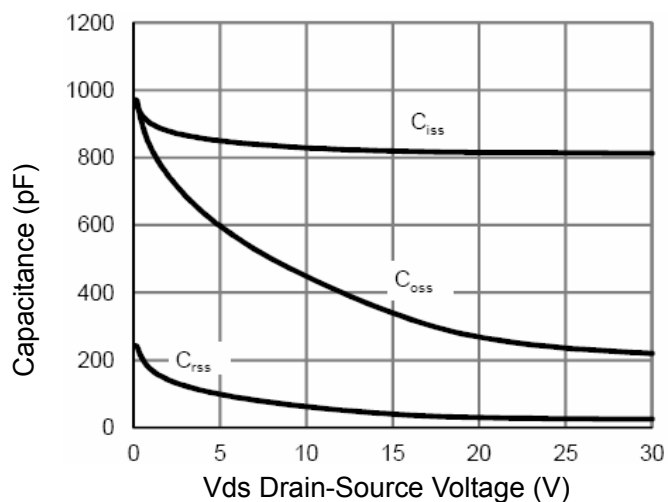


Figure 7 Capacitance vs Vds

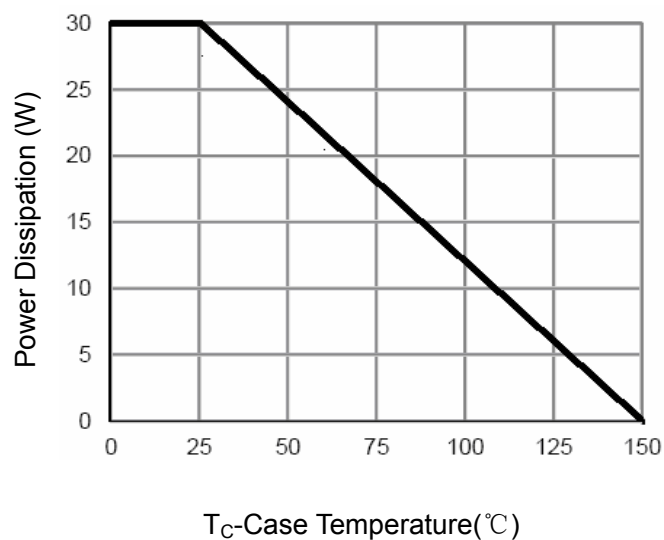


Figure 9 Power De-rating

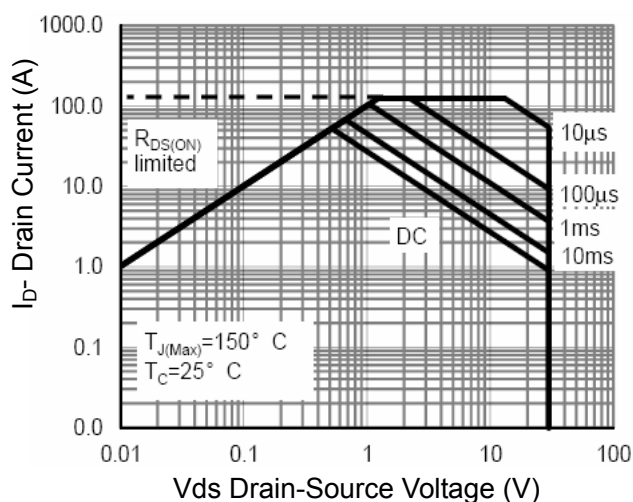


Figure 8 Safe Operation Area

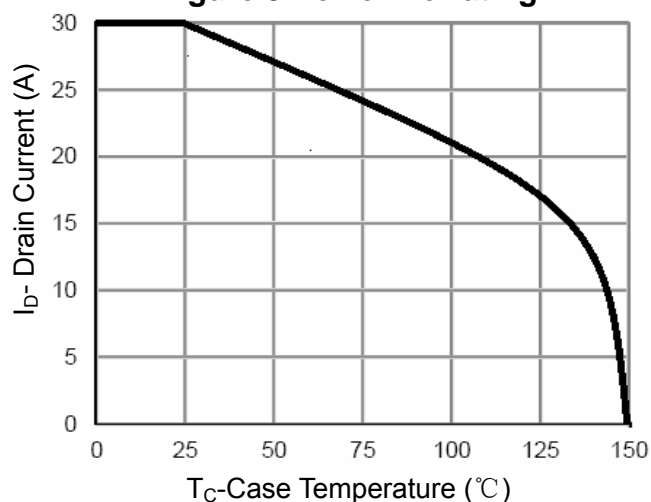


Figure 10 Current De-rating

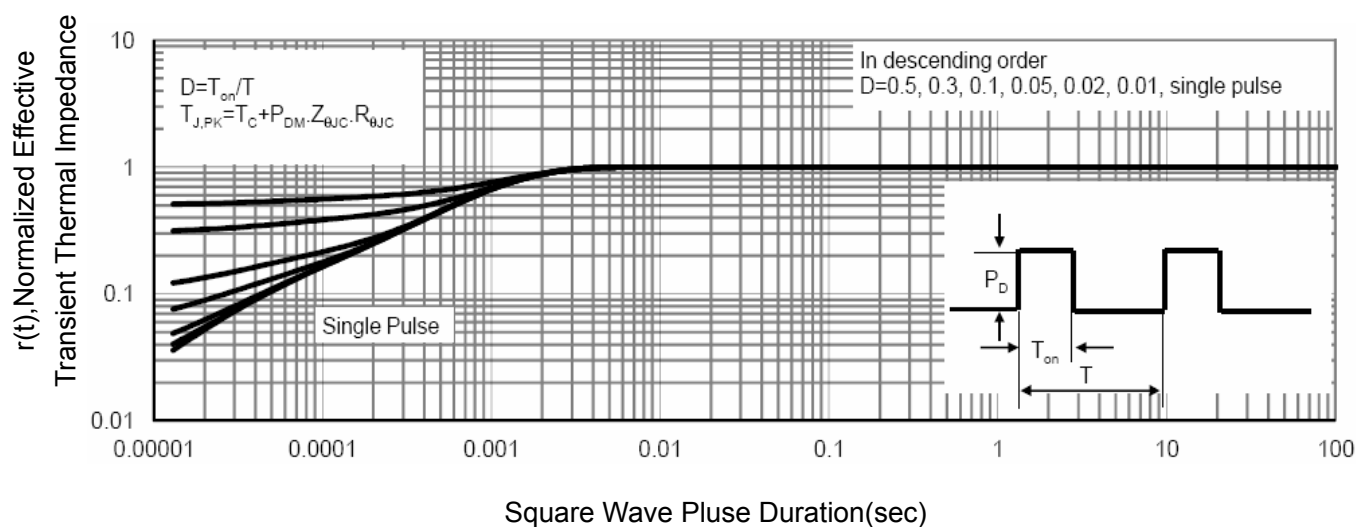


Figure 11 Normalized Maximum Transient Thermal Impedance

Q2 Electrical Characteristics (TC=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	10		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±10	μA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	1.5	2.2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =50A	-	12.9	16	mΩ
		V _{GS} =4.5V, I _D =50A	-	18.9	24	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =50A		65	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{ISS}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	3370	-	PF
Output Capacitance	C _{OSS}		-	902	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	60	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, I _D =50A V _{GS} =10V, R _G =1.6Ω	-	7	-	nS
Turn-on Rise Time	t _r		-	5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	32	-	nS
Turn-Off Fall Time	t _f		-	9	-	nS
Total Gate Charge	Q _g	V _{DS} =15V, I _D =50A, V _{GS} =10V	-	55	-	nC
Gate-Source Charge	Q _{gs}		-	9		nC
Gate-Drain Charge	Q _{gd}		-	8.5		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =50A	-		1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	40	mA
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = I _S di/dt = 500A/μs ^(Note3)	-	20	-	nS
Reverse Recovery Charge	Q _{rr}		-	50	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^\circ C, V_{DD}=15V, V_G=10V, L=0.5mH, R_g=25\Omega$

Q2 Typical Electrical and Thermal Characteristics

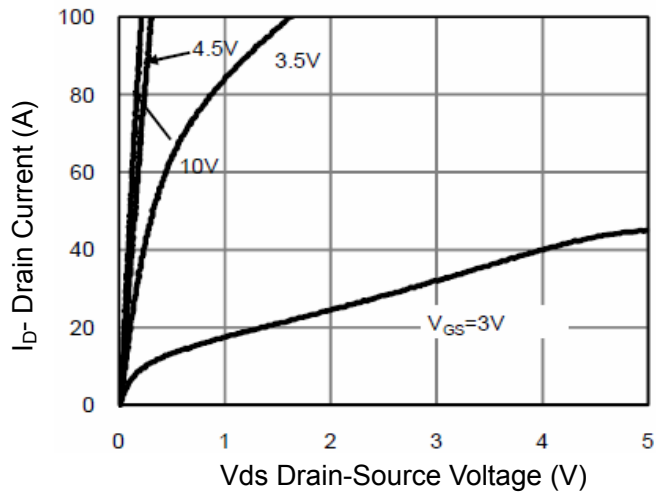


Figure 1 Output Characteristics

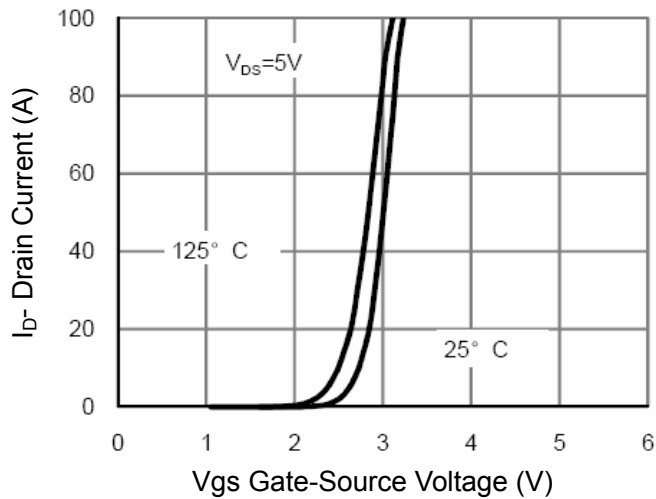


Figure 2 Transfer Characteristics

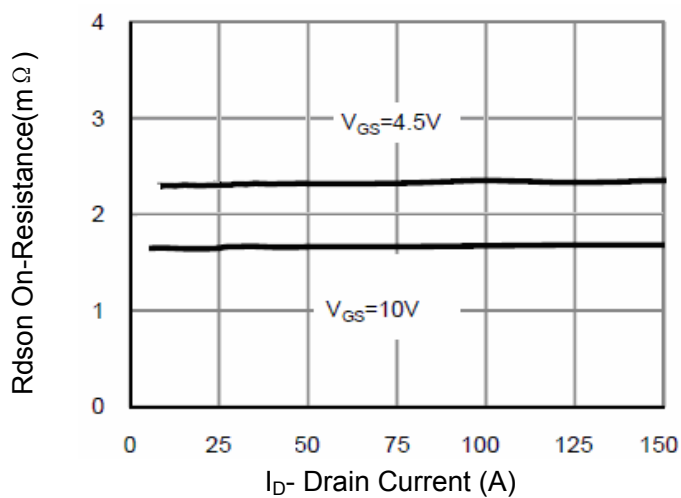


Figure 3 Rdson- Drain Current

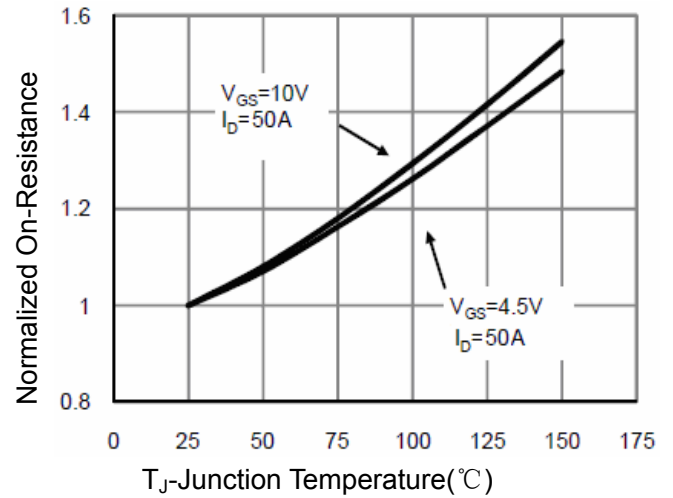


Figure 4 Rdson-Junction Temperature

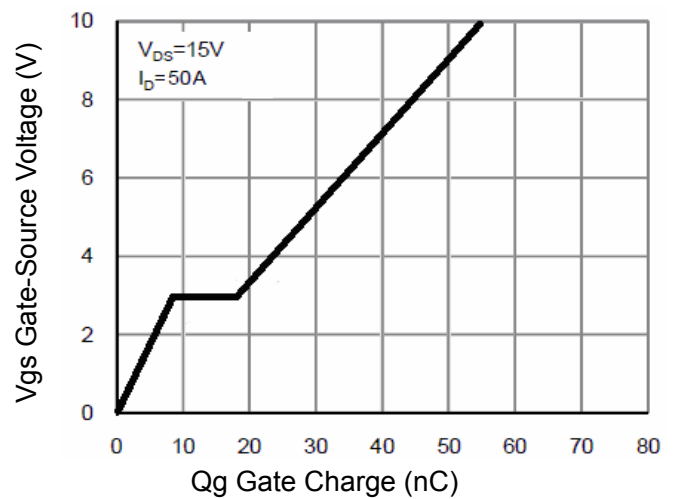


Figure 5 Gate Charge

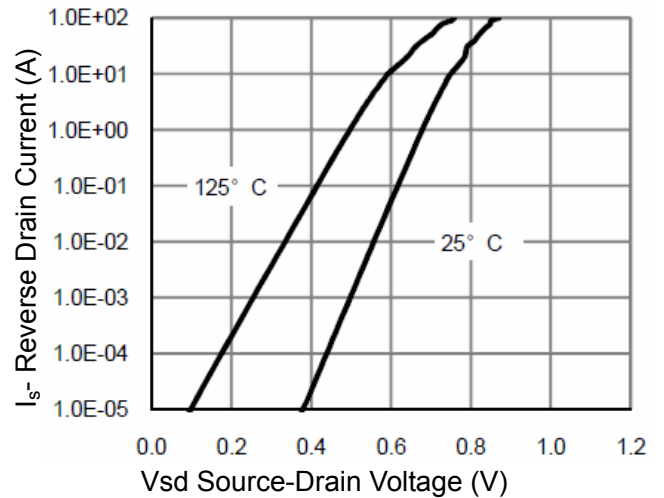


Figure 6 Source- Drain Diode Forward

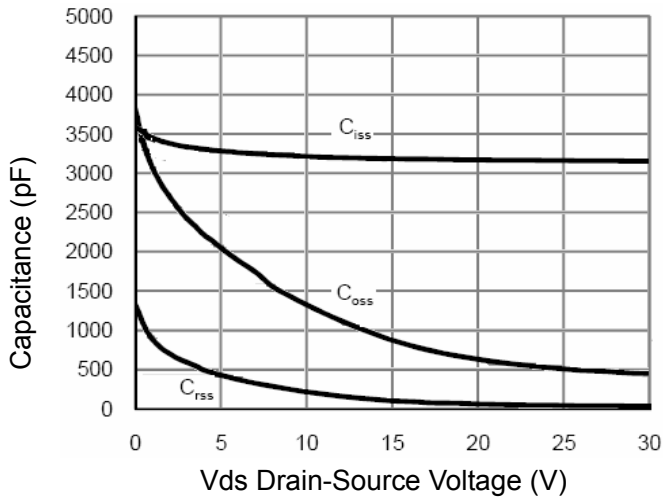


Figure 7 Capacitance vs Vds

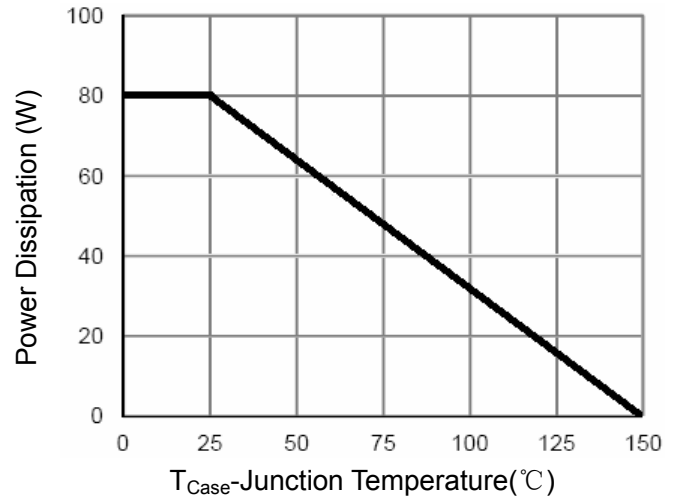


Figure 9 Power De-rating

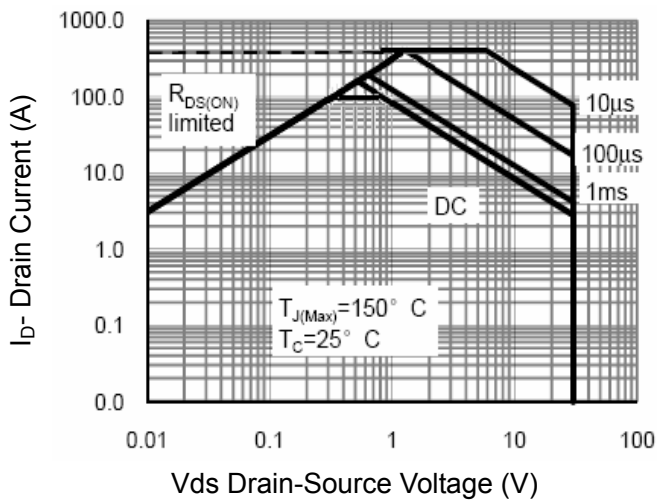


Figure 8 Safe Operation Area

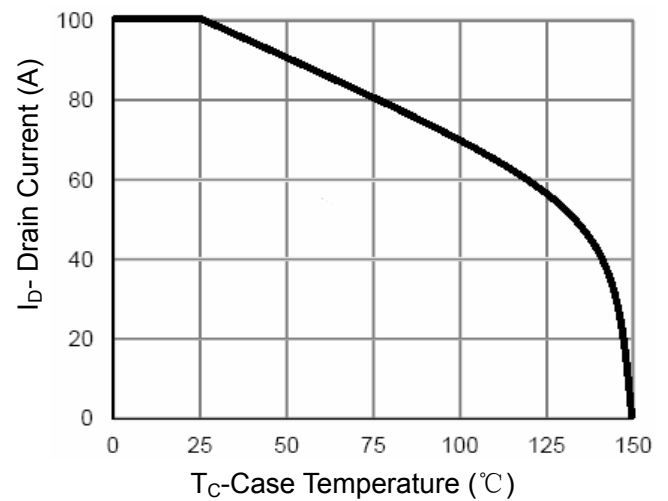


Figure 10 Current De-rating

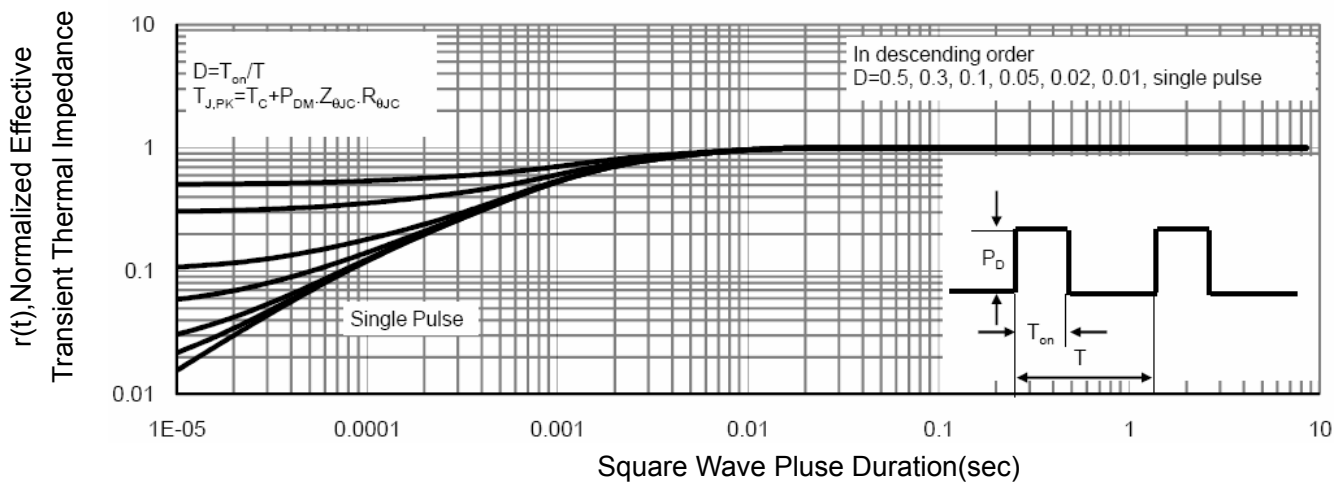
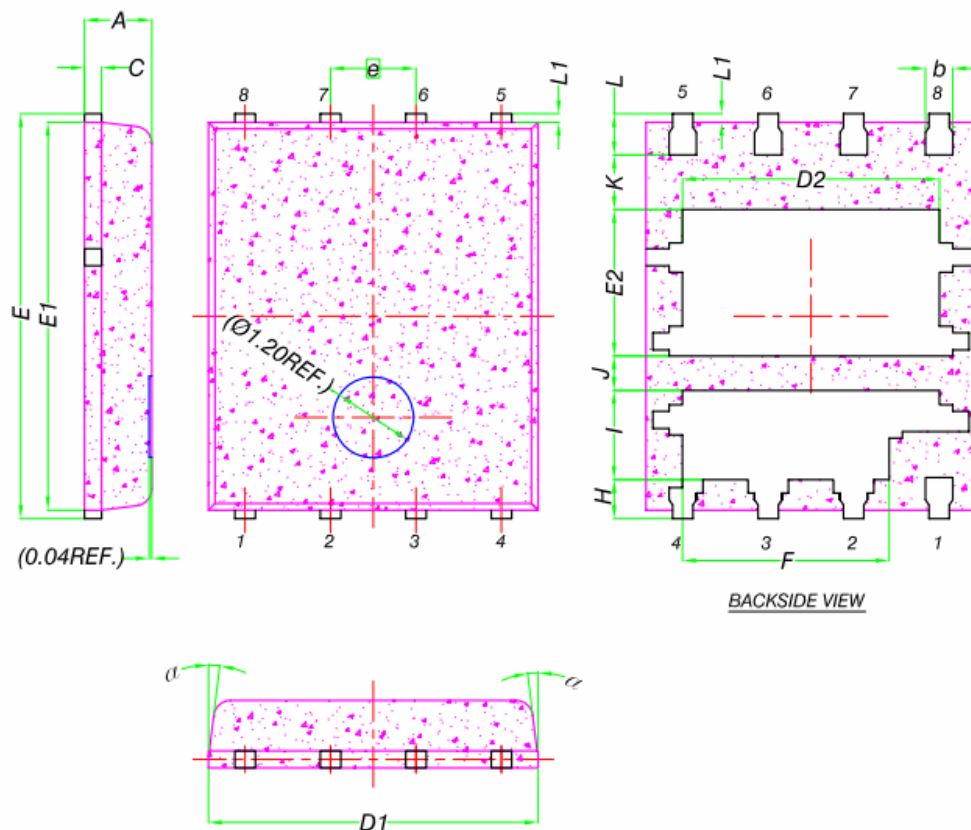


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN5X6-8L Package Information



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	2.02	2.17	2.32
e	1.27 BSC		
F	2.87	3.07	3.22
H	0.48	0.58	0.68
I	1.22	1.32	1.42
J	0.40	0.50	0.60
K	0.50	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°

Land Pattern
(Only for Reference)

